

SCHEMATIC (see Page 2)

UNITS FOR MODEL PARAMETERS

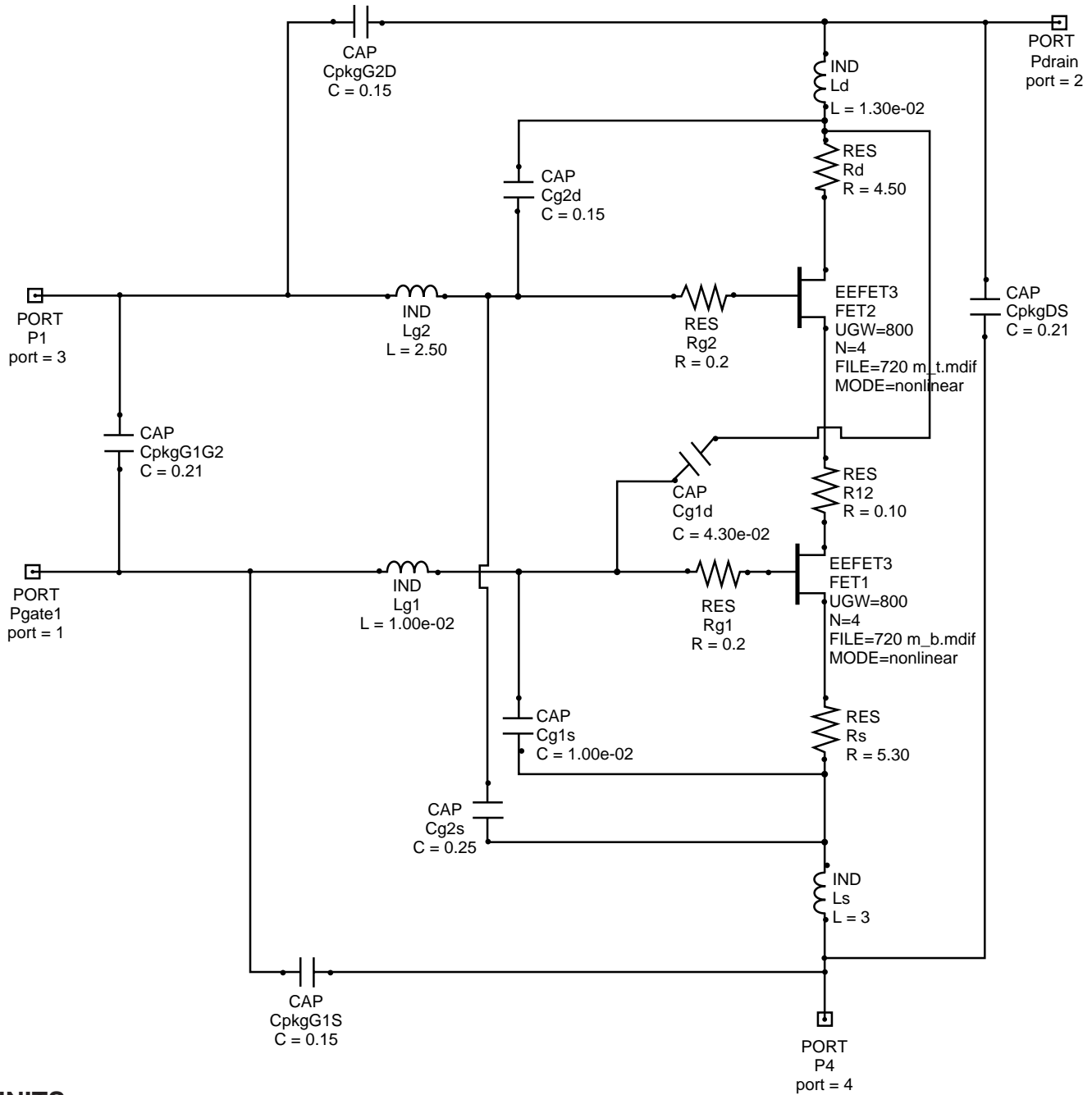
Parameter	Units
time	seconds
capacitance	farads
inductance	henries
resistance	ohms
voltage	volts
current	amps

FET NONLINEAR MODEL PARAMETERS⁽¹⁾

Parameters	FET1	FET2	Parameters	FET1	FET2
UGW	100e-6	100e-6	IDSOC	0.07	0.07
NGF	4	4	RDB	1.0e9	1.0e9
IS	8.78e-10	8.78e-10	CBS	0.16e-12	0.16e-12
N	1.33	1.33	GDBM	0.00035	0
RG	0	0	KDB	0	0
RD	0	0	VDSM	1	1
RS	0	0	GMMAXAC	0.0195	0.0394
RIS	0	0	GAMMAAC	0.006	0.06
RID	0	0	KAPAAC	0.95	0.95
TAU	1.0e-12	1.0e-12	PEFFAC	1.67	2.07
CDSO	5.0e-15	5.0e-15	VTOAC	-1.895	-1.895
C11O	0.25e-12	0.5e-12	VTSOAC	-10	-10
C11TH	0.1e-12	0.1e-12	VDELTA	3	3
VINFL	-1.12	-1.12	GMMAX	0.0294	0.0394
DELTGS	1.2	1.2	GAMMA	0.005	0.006
DELTD	1	0.1	KAPA	0.8	0.026
LAMBDA	0.25	0.25	PEFF	1.636	1.636
C11DELT	0	0	VTO	-2	-2
C12O	0	0	VTSO	-10	-10
C12SAT	0.01e-12	0.01e-12	VDELTA	1.47	1.47
CGDSAT	1.0e-15	1.0e-15	VCH	1	1
KBK	0.03	0.03	VSAT	3	3
VBR	6.5	6.5	VGO	1.47	1.47
NBR	2	2	VDSO	3	3

(1) Libra EEFET3 Model

SCHEMATIC



UNITS

Parameter	Units
capacitance	picofarads
inductance	nanohenries
resistance	ohms

NOTES:

1. This UGW value scales the model parameters on page 1.
2. This N value is the number of gate fingers and scales the model parameters on page 1.

Frequency: 0.1 to 1.5 GHz
 Bias: $V_{DS} = 3\text{ V}$, $V_{g1s} = -1.45\text{ V}$, $V_{g2s} = 1\text{ V}$, $I_D = 3\text{ mA}$

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CEL CALIFORNIA EASTERN LABORATORIES • Headquarters • 4590 Patrick Henry Drive • Santa Clara, CA 95054-1817 • (408) 988-3500 • Telex 34-6393 • FAX (408) 988-0279
 24-Hour Fax-On-Demand: 800-390-3232 (U.S. and Canada only) • Internet: <http://WWW.CEL.COM>

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